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65 V, 100 mA NPN/NPN general-purpose transistor Rev. 01 — 17 July 2009 Produ

Product data sheet

Product profile

1.1 General description

NPN/NPN general-purpose transistor pair in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- AEC-Q101 qualified

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	65	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	300	450	



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2. Pinning information

Table 2. Pinning

Table 2.	Filling		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1	D. D. D.	
2	base TR1	<u> </u>	6 5 4
3	collector TR2	0	TR2
4	emitter TR2	1 12 13	(TR1)
5	base TR2		
6	collector TR1		1 2 3
			sym020

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC846DS	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes

Type number	Marking code
BC846DS	ZK

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

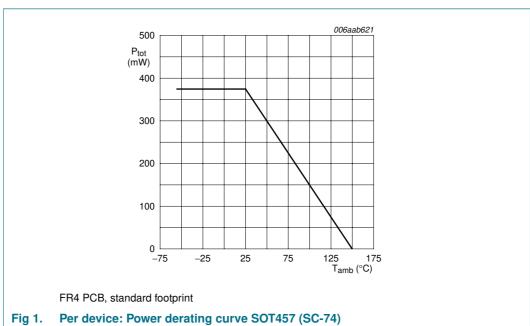
Symbol	Parameter	Conditions	Min	Max	Unit		
Per transis	Per transistor						
V_{CBO}	collector-base voltage	open emitter	-	80	V		
V_{CEO}	collector-emitter voltage	open base	-	65	V		
V_{EBO}	emitter-base voltage	open collector	-	6	V		
I _C	collector current		-	100	mA		
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA		
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u> _	250	mW		
Per device							
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	380	mW		

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Table 5. Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T_j	junction temperature		-	150	°C
T _{amb}	ambient temperature		– 55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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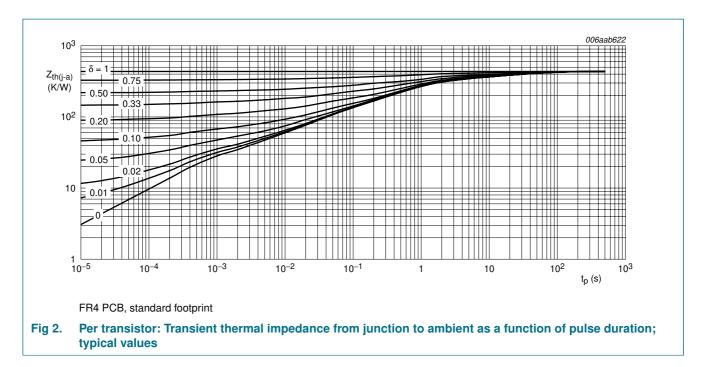
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	250	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	328	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

65 V, 100 mA NPN/NPN general-purpose transistor



7. Characteristics

Table 7. Characteristics

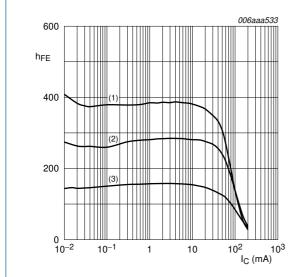
T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I _{CBO}	collector-base cut-off	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	15	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
h _{FE} DC current gain		$V_{CE} = 5 V$				
		$I_C = 10 \mu A$	-	280	-	
		$I_C = 2 \text{ mA}$	200	300	450	
V _{CEsat}	collector-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	55	100	mV
	saturation voltage	I _C = 100 mA; I _B = 5 mA	-	200	300	mV
V _{BEsat}	base-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	755	850	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	-	1000	-	mV
V_{BE}	base-emitter voltage	V _{CE} = 5 V				
		$I_C = 2 \text{ mA}$	580	650	700	mV
		I _C = 10 mA	-	-	770	mV

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Table 7. Characteristics ...continued $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	-	1.9	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz	-	11	-	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	100	-	-	MHz
NF	noise figure	$\begin{split} &V_{CE}=5~V;~I_{C}=0.2~mA;\\ &R_{S}=2~k\Omega;\\ &f=10~Hz~to~15.7~kHz \end{split}$	-	1.9	-	dB
		$\begin{split} &V_{CE}=5~V;~I_{C}=0.2~mA;\\ &R_{S}=2~k\Omega;~f=1~kHz;\\ &B=200~Hz \end{split}$	-	3.1	-	dB



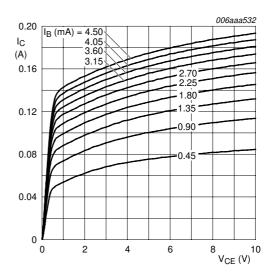
 $V_{CE} = 5 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

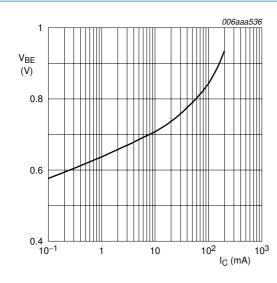
Fig 3. Per transistor: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

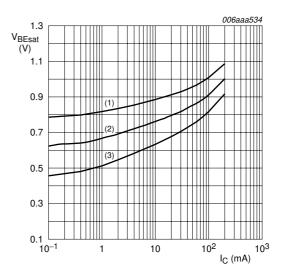
Fig 4. Per transistor: Collector current as a function of collector-emitter voltage; typical values

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 $V_{CE} = 5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$

Fig 5. Per transistor: Base-emitter voltage as a function of collector current; typical values



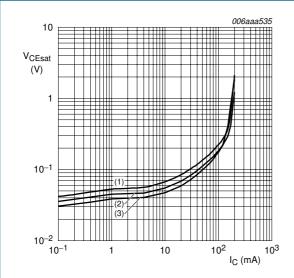
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values



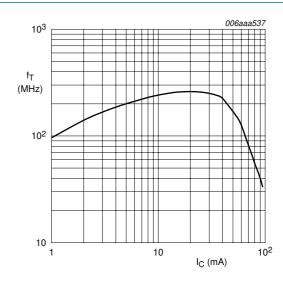
 $I_{C}/I_{B} = 20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = 5 \text{ V}; T_{amb} = 25 \,^{\circ}\text{C}$$

Fig 8. Per transistor: Transition frequency as a function of collector current; typical values

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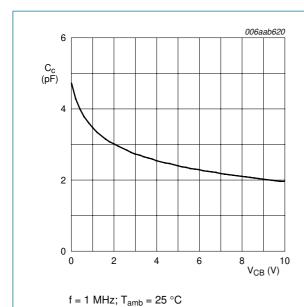


Fig 9. Per transistor: Collector capacitance as a function of collector-base voltage; typical values

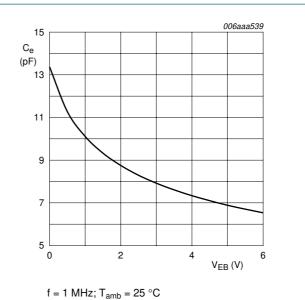


Fig 10. Per transistor: Emitter capacitance as a function of emitter-base voltage; typical values

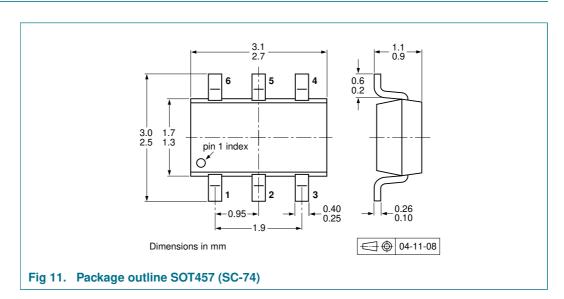
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8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BC846DS	SOT457	4 mm pitch, 8 mm tape and reel; T1	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-165

^[1] For further information and the availability of packing methods, see Section 14.

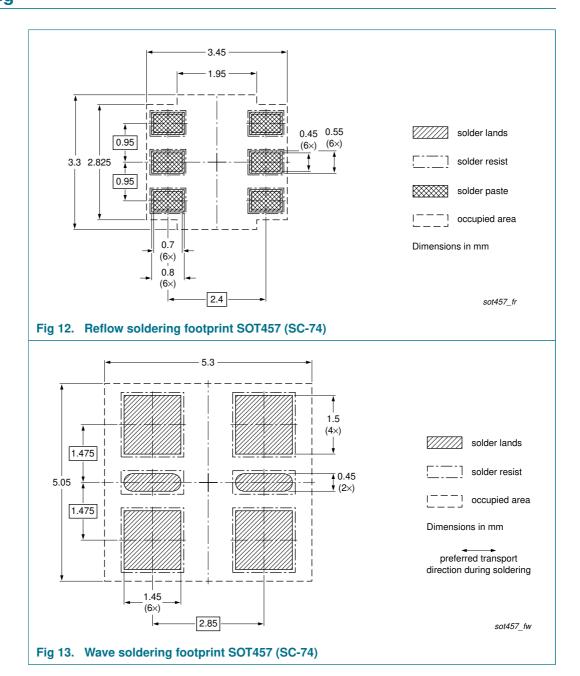
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^[2] T1: normal taping

^[3] T2: reverse taping

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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC846DS_1	20090717	Product data sheet	-	-

65 V, 100 mA NPN/NPN general-purpose transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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